

Changes to Claims:

Please replace claims 1-13 as follows:

1. (Amended) A producing method of a mask which produces a phase-shift mask and a correction exposure mask used when a transmission image of a pattern of the phase-shift mask is corrected by superimposing exposure, comprising:

forming a parent pattern on a first substrate to form a master mask;

transferring the parent pattern of the master mask onto a second substrate under a first condition, and forming a predetermined phase shift portion on the second substrate, thereby forming the phase-shift mask; and

transferring the parent pattern of the master mask onto a third substrate under a second condition which is different from the first condition, thereby forming the correction exposure mask.

2. (Amended) A producing method of a mask as recited in claim 1, wherein the second condition is a condition wherein an amount of exposure is smaller than that in the first condition.

3. (Amended) A producing method of a mask as recited in claim 1, wherein under the first condition, the parent pattern of the master mask is transferred onto the second substrate through a first projection optical system having a predetermined first resolution, and

under the second condition, the parent pattern of the master mask is transferred onto the third substrate through a second projection optical system having a second resolution lower than the first resolution.

4. (Amended) A producing method of a mask as recited in claim 3, wherein the numerical aperture of the second projection optical system used under the second condition is set smaller than the numerical aperture of the first projection optical system used under the first condition.

5. (Amended) A producing method of a mask as recited in claim 1, wherein under the second condition, the third substrate is defocused with respect to an image plane of the projection optical system.

6. (Amended) A producing method of a mask as recited in claim 1, wherein the parent pattern is divided into the plural number to form a plurality of master masks, and patterns of the plurality of the master masks are transferred while stitching screens, thereby forming patterns respectively corresponding to the parent pattern on the second and third substrates.

7. (Amended) A producing method of a mask which produces a correction exposure mask used when a transmission image of a pattern of a predetermined phase-shift mask is corrected by superimposing exposure, comprising:

forming a parent pattern on a first substrate to produce a master mask; and

transferring the parent pattern of the master mask onto a second substrate under a condition different from a condition under which a light shield pattern of the phase-shift mask is formed, thereby forming the correction exposure mask.

8. (Amended) A producing method of a mask as recited in claim 7, wherein the condition includes at least one of an exposure amount, a resolution, and focus.

9. (Amended) A producing apparatus of a mask which produces a plurality kinds of masks different from one another, comprising:

a mask stage which holds a master mask on which a parent pattern is formed;

a substrate stage which sequentially holds and positions a plurality of mask substrates for the masks;

an illumination optical system which illuminates the master masks on the mask stage;

a projection optical system which transfers an image of the parent pattern of the master mask onto the mask substrate on the substrate stage; and

a control system which adjusts at least one of an exposure amount with respect to the mask substrate and a resolution of the projection optical system in accordance with kinds of the mask to be produced.

10. (Amended) A producing method of a predetermined device, comprising:

drawing a parent pattern corresponding to a pattern of a predetermined layer of the device onto one or a plurality of first substrates to form a master mask;

transferring the parent pattern of the master mask onto a second substrate under a first condition and forming a predetermined phase-shift portion on the second substrate, thereby forming a phase-shift mask;

transferring the parent pattern of the master mask onto a third substrate under a second condition which is different from the first condition, thereby forming a correction exposure mask; and

exposing in a superimposing manner the pattern of the phase-shift mask and the pattern of the correction exposure mask on a fourth substrate.

11. (Amended) A photomask produced using the mask producing method as recited in claim 1.

12. (Amended) A producing method of a device, comprising: transferring a device pattern onto a device substrate using the mask as recited in claim 11.

13. (Amended) A photomask produced using the mask producing apparatus as recited in claim 9.

Please add new claims 14-18 as follows:

--14. A producing method of a mask used for double exposure of a photosensitive substrate, comprising: transferring a parent pattern of a master mask onto a first substrate to produce a first mask used for one exposure of the double exposure, and transferring the parent pattern of the master mask onto a second substrate to produce a second mask used for the other exposure of the double exposure, wherein a condition under which the parent pattern of